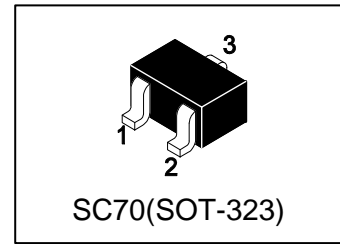


LBAT54WT1G

S-LBAT54WT1G

Schottky Barrier Diode



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Extremely Fast Switching Speed
- Low Forward Voltage — 0.35 Volts (Typ) @ IF = 10 Ma

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAT54WT1G	B4	3000/Tape&Reel
LBAT54WT3G	B4	10000/Tape&Reel

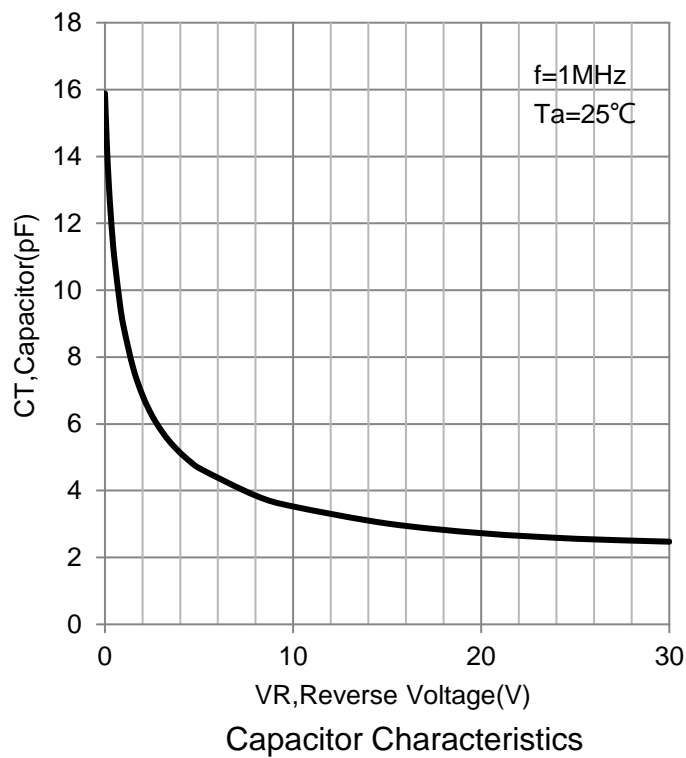
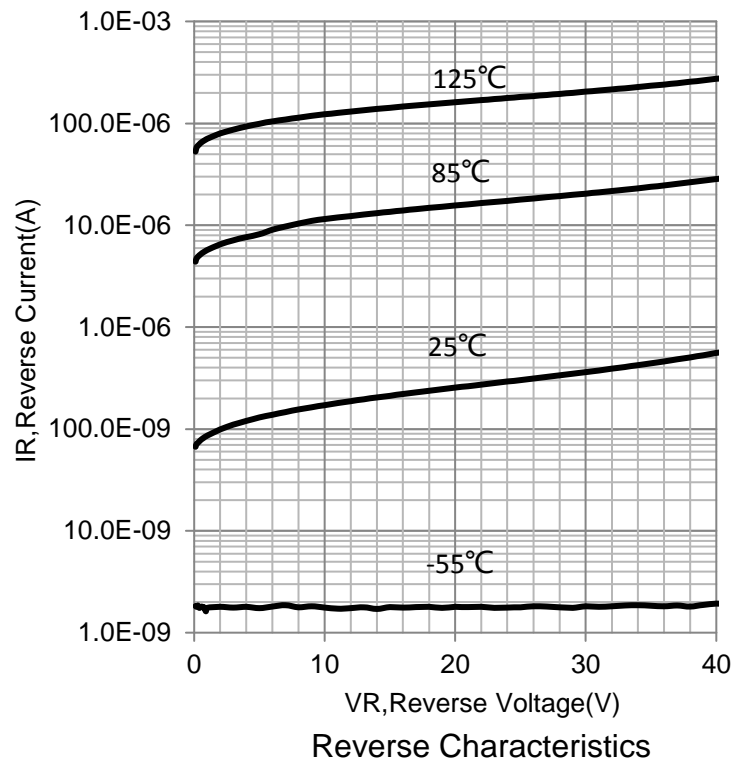
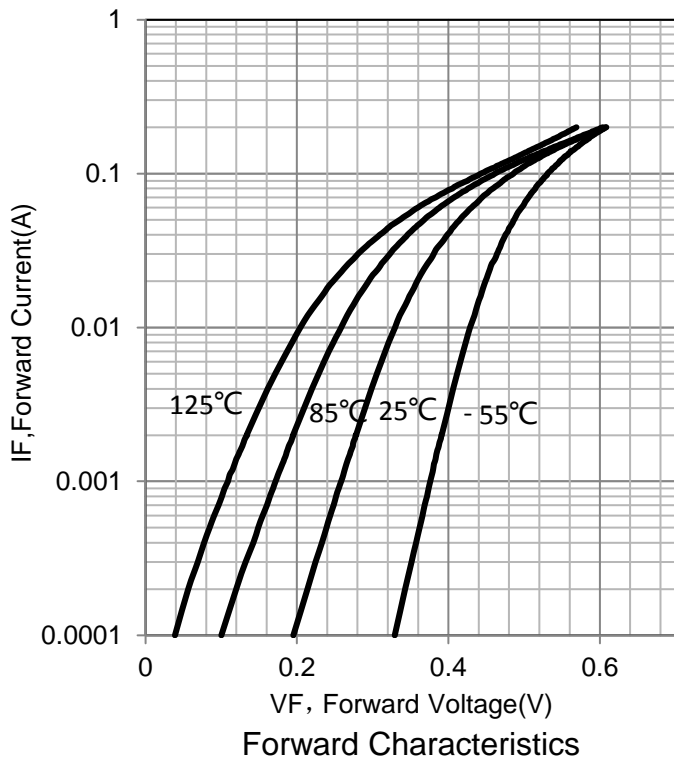
3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage	VR	30	V
Forward Power Dissipation @ TA = 25°C	PD	200	mW
Derate above 25°C		1.6	mW/°C
Forward Current (DC)	IF	200	mA
Junction temperature	Tj	-55~+125	°C
Storage Temperature Range	Tstg	-55~+150	°C
Thermal Resistance Junction-to-Ambient	RθJA	625	°C/W

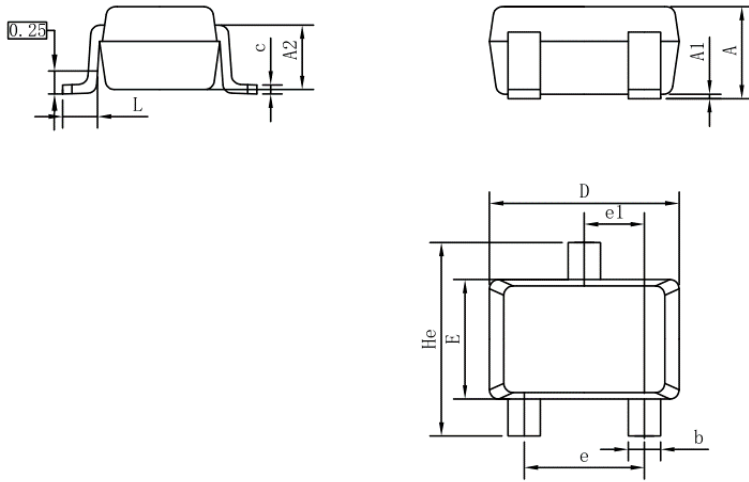
4. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage (IR = 10μA)	VBR	30	-	-	V
Diode Capacitance (VR =1.0V , f = 1.0 MHz)	CT	-	10	-	pF
Reverse Voltage Leakage Current (VR = 25V)	IR	-	0.5	2	μA
Forward Voltage (IF = 0.1 mA)	VF	-	0.22	0.24	V
(IF = 1 mA)		-	0.29	0.32	
(IF = 10 mA)		-	0.35	0.4	
(IF = 30 mA)		-	0.41	0.5	
(IF = 100 mA)		-	0.52	1	
Forward Current (DC)	IF	-	-	200	mA
Repetitive Peak Forward Current	IFRM	-	-	300	
Non-Repetitive Peak Forward Current (t < 1.0 s)	IFSM	-	-	600	

5. ELECTRICAL CHARACTERISTICS CURVES

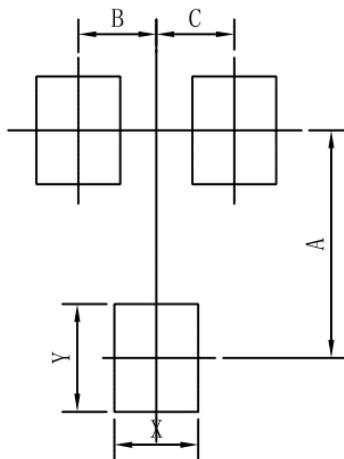


6. OUTLINE AND DIMENSIONS



SC70			
DIM	MIN	NOR	MAX
A	0.80	0.95	1.00
A1	0.00	0.05	0.10
A2	0.7 REF		
b	0.30	0.35	0.40
c	0.10	0.15	0.25
D	1.80	2.05	2.20
E	1.15	1.30	1.35
e	1.20	1.30	1.40
e1	0.65 BSC		
L	0.20	0.35	0.56
He	2.00	2.10	2.40
ALL Dimension in mm			

7. SOLDERING FOOTPRINT



SC70	
DIM	MIN
A	1.90
B	0.65
C	0.65
X	0.70
Y	0.90